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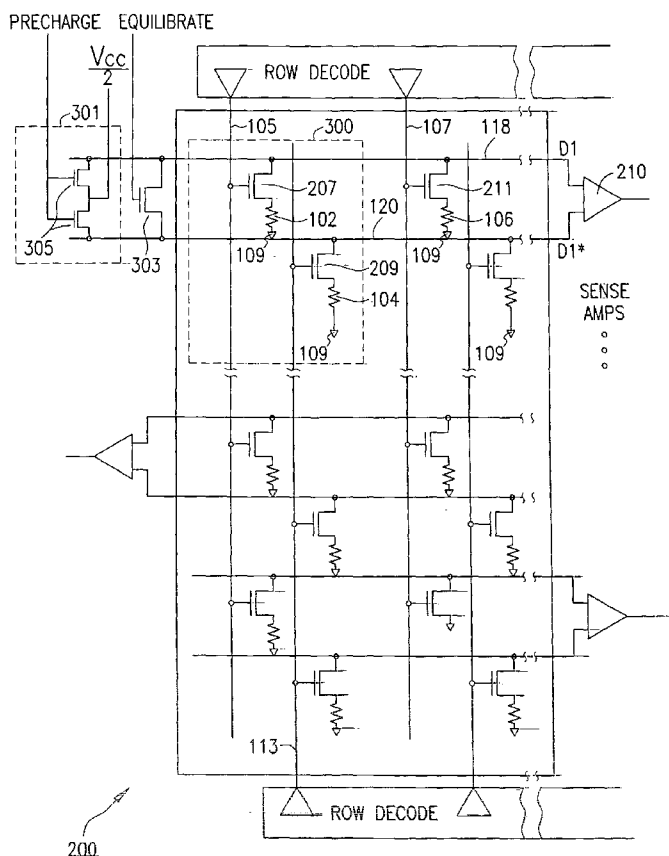
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(54) Title: COMPLEMENTARY BIT PCRAM (PROGRAMMABLE CONDUCTOR RAM) AND METHOD OF OPERATION



(57) Abstract: A method and apparatus is disclosed for sensing the resistance state of a Programmable Conductor Random Access Memory (PCRAM) element using complementary PCRAM elements, one holding the resistance state being sensed and the other holding a complementary resistance state. A sense amplifier detects voltages discharging through the high and low resistance elements to determine the resistance state of an element being read.



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